













CSD18513Q5A

SLPS623A - NOVEMBER 2016-REVISED JANUARY 2017

CSD18513Q5A 40-V N-Channel NexFET™ Power MOSFET

Features

- Low R_{DS(ON)}
- Low-Thermal Resistance
- Avalanche Rated
- Logic Level
- Lead-Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

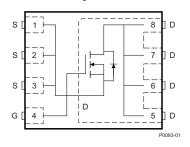
Applications

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- **Battery Motor Control**

3 Description

This 40-V, 2.8-mΩ, 5-mm × 6-mm SON NexFET™ power MOSFET is designed to minimize losses in power conversion applications.





R_{DS(on)} vs V_{GS} T_C = 25℃, I_D = 19 A R_{DS(on)} - On-State Resistance (mΩ) $T_C = 125$ °C, $I_D = 19$ A 10 2 0 0 10 12 20 V_{GS} - Gate-to-Source Voltage (V)

Product Summary

$T_A = 25^\circ$	С	TYPICAL VA	UNIT		
V_{DS}	Drain-to-Source Voltage 40				
Q_g	Gate Charge Total (10 V)	45		nC	
Q_{gd}	Gate Charge Gate-to-Drain	8.8		nC	
D	Drain-to-Source On Resistance	V _{GS} = 4.5 V	4.1	mΩ	
R _{DS(on)}	Drain-to-Source On Resistance	V _{GS} = 10 V	2.8	11177	
V _{GS(th)}	Threshold Voltage	1.8		V	

Device Information⁽¹⁾

DEVICE	MEDIA	QTY	PACKAGE	SHIP
CSD18513Q5A	13-Inch Reel	2500	SON	Tape
CSD18513Q5AT	7-Inch Reel	250	5.00-mm x 6.00-mm Plastic Package	and Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

Absolute Maximum Rutings							
5°C	VALUE	UNIT					
Drain-to-Source Voltage	40	V					
Gate-to-Source Voltage	±20	V					
Continuous Drain Current (Package Limited)	100						
Continuous Drain Current (Silicon Limited), T _C = 25°C	124	Α					
Continuous Drain Current ⁽¹⁾	22						
Pulsed Drain Current ⁽²⁾	400	Α					
Power Dissipation ⁽¹⁾	3.1	101					
Power Dissipation, T _C = 25°C	96	W					
Operating Junction, Storage Temperature	-55 to 150	°C					
Avalanche Energy, Single Pulse I _D = 46 A, L = 0.1 mH, R _G = 25 Ω	106	mJ					
	Drain-to-Source Voltage Gate-to-Source Voltage Continuous Drain Current (Package Limited) Continuous Drain Current (Silicon Limited), T _C = 25°C Continuous Drain Current ⁽¹⁾ Pulsed Drain Current ⁽²⁾ Power Dissipation ⁽¹⁾ Power Dissipation, T _C = 25°C Operating Junction, Storage Temperature Avalanche Energy, Single Pulse	Drain-to-Source Voltage Drain-to-Source Voltage Gate-to-Source Voltage Continuous Drain Current (Package Limited) Continuous Drain Current (Silicon Limited), T _C = 25°C Continuous Drain Current ⁽¹⁾ Pulsed Drain Current ⁽²⁾ Power Dissipation ⁽¹⁾ Power Dissipation, T _C = 25°C Operating Junction, Storage Temperature Avalanche Energy, Single Pulse					

- (1) Typical $R_{\theta JA} = 40^{\circ}\text{C/W}$ on a 1-in², 2-oz Cu pad on a 0.06-in thick FR4 PCB.
- (2) Max $R_{\theta,JC} = 1.3^{\circ}C/W$, pulse duration $\leq 100 \mu s$, duty cycle \leq

Gate Charge

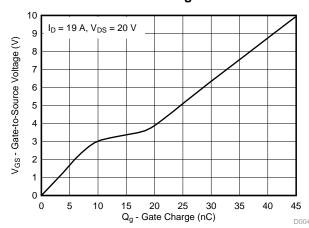




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4 Revision History

Cł	hanges from Original (November 2016) to Revision A	Page
•	Changed the charge values in the Dynamic Characteristics section of the <i>Electrical Characteristics</i> table	3
•	Changed Figure 4 in the Typical MOSFET Characteristics section to reflect updated gate charges	4

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5 Specifications

5.1 Electrical Characteristics

 $T_A = 25$ °C (unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN T	YP MAX	UNIT
STATIC	CHARACTERISTICS		'		
BV _{DSS}	Drain to-source voltage	V _{GS} = 0 V, I _D = 250 μA	40		V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 32 V		1	μА
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 20 V		100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5	1.8 2.4	V
D	Drain to course on registence	$V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$		4.1 5.3	mΩ
R _{DS(on)}	Drain-to-source on resistance	V _{GS} = 10 V, I _D = 19 A		2.8 3.4	11122
g _{fs}	Transconductance	$V_{DS} = 4 \text{ V}, I_{D} = 19 \text{ A}$		89	S
DYNAMI	C CHARACTERISTICS				
C _{iss}	Input capacitance		33	300 4280	pF
C _{oss}	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$;	333 433	pF
C _{rss}	Reverse transfer capacitance			178 231	pF
R_G	Series gate resistance			0.9 1.8	Ω
Qg	Gate charge total (4.5 V)			23 30	nC
Qg	Gate charge total (10 V)			45 59	nC
Q _{gd}	Gate charge gate-to-drain	V _{DS} = 20 V, I _D = 19 A		8.8	nC
Q _{gs}	Gate charge gate-to-source			9.1	nC
Q _{g(th)}	Gate charge at V _{th}			5.8	nC
Q _{oss}	Output charge	V _{DS} = 20 V, V _{GS} = 0 V		15	nC
t _{d(on)}	Turnon delay time			6	ns
t _r	Rise time	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V},$		12	ns
t _{d(off)}	Turnoff delay time	$I_{DS} = 19 \text{ A}, R_G = 0$		21	ns
t _f	Fall time			4	ns
DIODE C	CHARACTERISTICS				
V _{SD}	Diode forward voltage	I _{SD} = 19 A, V _{GS} = 0 V		0.8 1.0	V
Q _{rr}	Reverse recovery charge	V _{DS} = 20 V, I _F = 19 A,		12	nC
t _{rr}	Reverse recovery time	di/dt = 300 A/μs		12	ns

5.2 Thermal Information

 $T_A = 25^{\circ}C$ (unless otherwise stated)

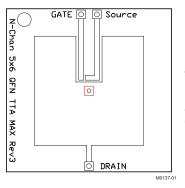
,,	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance ⁽¹⁾			1.3	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾⁽²⁾			50	°C/W

R_{θJC} is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 1.5-in x 1.5-in (3.81-cm x 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.

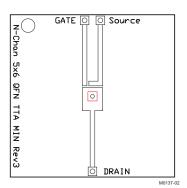
(2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.

Product Folder Links: CSD18513Q5A





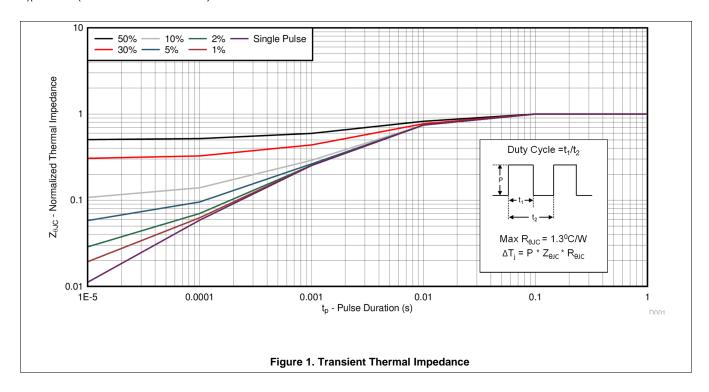
Max $R_{\theta JA} = 50^{\circ} C/W$ when mounted on 1 in² (6.45 cm²) of 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA} = 125^{\circ} C/W$ when mounted on a minimum pad area of 2-oz (0.071-mm) thick Cu.

5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C (unless otherwise stated)



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2.4

2.2

2

1.8

1.61.41.2

0.8

-75

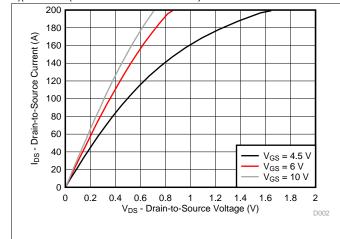
-50 -25 0 25 50

- Threshold Voltage (V)



Typical MOSFET Characteristics (continued)

 $T_A = 25^{\circ}C$ (unless otherwise stated)



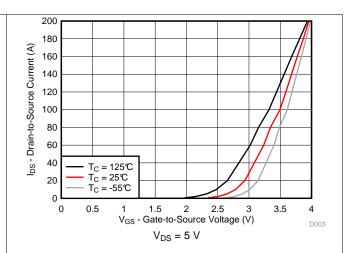
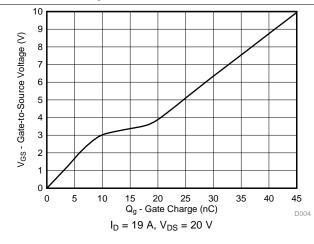


Figure 2. Saturation Characteristics





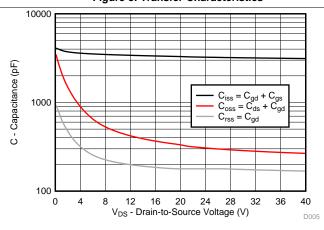


Figure 4. Gate Charge

75 100

125 150 175

Figure 5. Capacitance

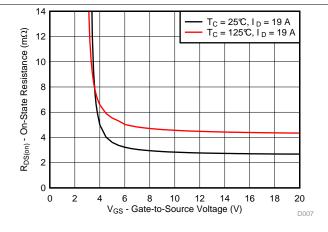


Figure 6. Threshold Voltage vs Temperature

 T_{C} - Case Temperature $(\ensuremath{\mathfrak{C}})$

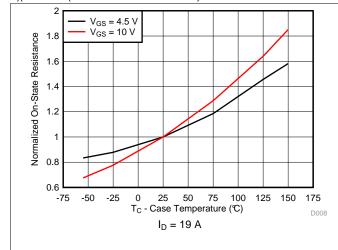
 $I_D = 250 \mu A$

Figure 7. On-State Resistance vs Gate-to-Source Voltage



Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C (unless otherwise stated)



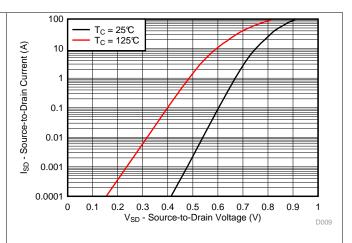
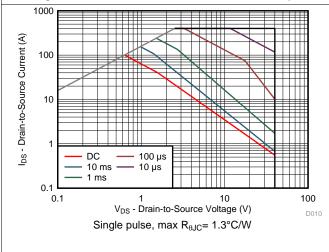


Figure 8. Normalized On-State Resistance vs Temperature





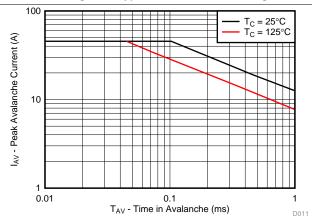


Figure 10. Maximum Safe Operating Area

Figure 11. Single Pulse Unclamped Inductive Switching

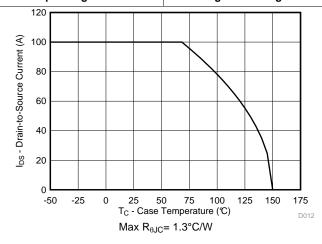


Figure 12. Maximum Drain Current vs Temperature

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6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 Trademarks

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6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

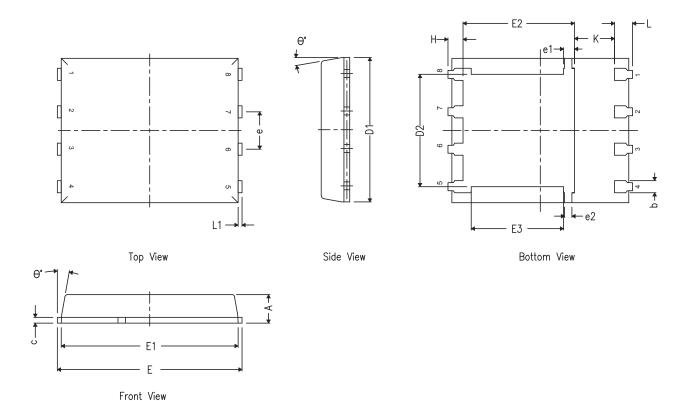
Product Folder Links: CSD18513Q5A



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q5A Package Dimensions

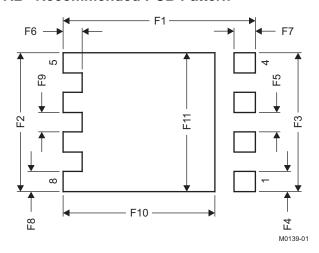


DIM	MIL	LIMETERS	
DIM	MIN	NOM	MAX
Α	0.90	1.00	1.10
b	0.33	0.41	0.51
С	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
E3	3.03	3.13	3.23
е	1.17	1.27	1.37
e1	0.27	0.37	0.47
e2	0.15	0.25	0.35
Н	0.41	0.56	0.71
K	1.10	_	1
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°	_	12°

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7.2 Recommended PCB Pattern



DIM	MILLIME:	TERS	INCH	IES
DIM	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	8.0	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

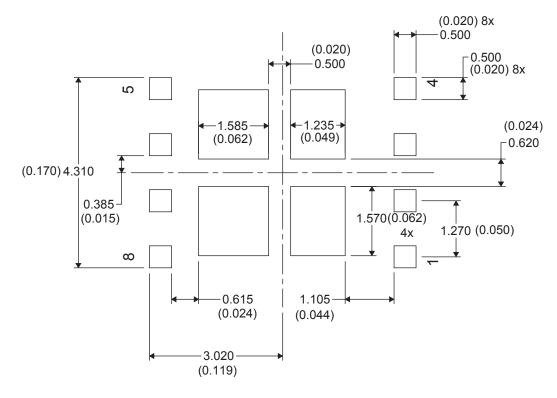
For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

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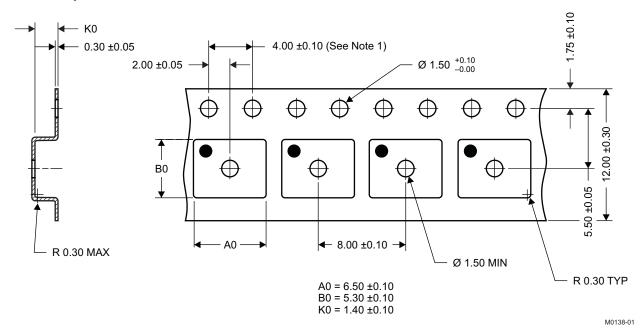
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7.3 Recommended Stencil Opening



7.4 Q5A Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2.
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm.
- 3. Material: black static-dissipative polystyrene.
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

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PACKAGE OPTION ADDENDUM

9-Jan-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD18513Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18513	Samples
CSD18513Q5AT	ACTIVE	VSONP	DQJ	8	250	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18513	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

9-Jan-2017

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